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November 2013

FDP020N06B — N-Channel PowerTrench[®] MOSFET

FDP020N06B N-Channel PowerTrench[®] MOSFET $60 V, 313 A, 2 m\Omega$

Features

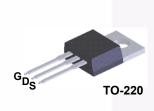
- $R_{DS(on)}$ = 1.65 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 100 A
- Low FOM R_{DS(on)} * Q_G
- Low Reverse-Recovery Charge, Q_{rr} = 194 nC
- Soft Reverse-Recovery Body Diode
- Enables High Efficiency in Synchronous Rectification
- · Fast Switching Speed
- 100% UIL Tested
- RoHS Compliant

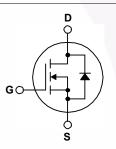
Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench[®] process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- Battery Protection Circuit
- Motor Drives and Uninterruptible Power Supplies
- Renewable System





Absolute Maximum Ratings T_C = 25°C unless otherwise noteed.

Symbol		Parameter	FDP020N06B_F102	Unit
V _{DSS}	Drain to Source Voltage	60	V	
V _{GSS}	Gate to Source Voltage		±20	V
I _D		- Continuous (T _C = 25 ^o C, Silicon Limited)	313*	A
	Drain Current	- Continuous (T _C = 100 ^o C, Silicon Limited)	221*	
		- Continuous (T _C = 25 ^o C, Package Limited)	120	1
I _{DM}	Drain Current	- Pulsed (Note 1)	1252	А
E _{AS}	Single Pulsed Avalanche Er	1859	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		6.0	V/ns
P _D F	Dower Dissinction	(T _C = 25°C)	333	W
	Power Dissipation	- Derate Above 25°C	2.2	W/ºC
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
ΤL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C

* Package limitation current is 120A.

Thermal Characteristics

Symbol	Parameter	FDP020N06B_F102	Unit
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	0.45	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	-0/00

Part Nun FDP020N06		Top Mark FDP020N06B	Package TO-220	Packing Method Tube	Reel Size N/A	Тар	be Width N/A	Quar 50 u	
Electrica	l Chara	acteristics T_c =	= 25ºC unless	otherwise noted.					
Symbol		Parameter		Test Condit	tions	Min.	Тур.	Max.	Unit
Off Charact	teristics	ن							
BV _{DSS}	Drain to ?	Source Breakdown V	/oltage	I _D = 250 μA, V _{GS} = 0 V		60	-	-	V
ΔBV _{DSS} / ΔΤ _J		wn Voltage Temperat	0	$I_D = 250 \ \mu$ A, Referenced to 25° C		-	0.03	-	V/ºC
	Zara Cal			$V_{DS} = 48 V, V_{GS} = 0 V$		-	-	1	
IDSS	Zero Gau	te Voltage Drain Curr	ent	$V_{DS} = 48 \text{ V}, \text{ T}_{C} = 150^{\circ}$	-Oc	-		500	μΑ
I _{GSS}	Gate to E	Body Leakage Currer	nt	V_{GS} = ±20 V, V_{DS} = 0	V	-	-	±100	nA
On Charact	teristics								
V _{GS(th)}		reshold Voltage		V _{GS} = V _{DS} , I _D = 250 μA		2.5	3.3	4.5	V
R _{DS(on)}		ain to Source On Res	sistance	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 100 \text{ A}$		_	1.65	2.0	mΩ
9 _{FS}		Transconductance		$V_{\rm DS} = 10 \text{ V}, \text{ I}_{\rm D} = 100 \text{ A}$		-	263	-	S
	baracto	riation							L
-	haracteristics					-	16100	20930	nE
Ciss		Input Capacitance Output Capacitance Reverse Transfer Capacitance				-	3840	4992	pF pF
C _{oss}				f = 1 MHz	F		127	4992	pF pF
C _{rss}	Reverse Transfer Capacitance Energy Related Output Capacitance			V _{DS} = 30 V, V _{GS} = 0 V		-	5897	-	pF pF
C _{oss(er)}	0,	te Charge at 10V	Jlance	$v_{\rm DS} = 30 v, v_{\rm GS} = 0 v$	-	206	- 268	nC	
Q _{g(tot)} Q _{gs}		Source Gate Charge				-	87	- 200	nC
Q _{gs} Q _{gs2}	-	Threshold to Plateau		V _{DS} = 30 V, I _D = 100 A, V _{GS} = 10 V	А,	_	36	_	nC
Q _{gs2} Q _{gd}		Drain "Miller" Charge		VGSIO U	(Note 4)	_	34	_	nC
ESR	Equivalent Series Resistance(G-S)			f = 1 MHz		-	0.9	-	Ω
Switching (Charact	oristics		-	I		1	1	
-	1					-	74	158	ns
t _{d(on)} t _r	Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time			$V_{DD} = 30 \text{ V}, \text{ I}_{D} = 100 \text{ A},$ $V_{GS} = 10 \text{ V}, \text{ R}_{G} = 4.7 \Omega$			62	134	ns
							112	234	ns
t _{d(off)} t _f		Fall Time		-	(Note 4)	<u> </u>	42	94	ns
					(11018 4)		72	54	113
		e Characteristic						313*	A
l _S		n Pulsed Drain to Sou				-		1252	A
I _{SM} V _{SD}		Source Diode Forwar		$V_{GS} = 0 V, I_{SD} = 100 A$				1.25	V
t _{rr}	Reverse Recovery Time		a voltage	$V_{GS} = 0 V, V_{DD} = 30 V, I_{SD} = 100 A,$		-	106	-	ns
Q _{rr}	Reverse Recovery Charge			$dI_{F}/dt = 100 A/\mu s$		-	194	-	nC
Notes: 1: Repetitive rating 2: Starting $T_J = 25^{\circ}$ 3: $I_{SD} \le 100 \text{ A, di/d}$	°C, L = 3 mH, I It ≤ 200 A/µs, \	limited by maximum junction $I_{AS} = 35.2 \text{ A}$ $V_{DD} \le BV_{DSS}$, starting $T_J = 2$ erating temperature typical c	25°C					E	9

Figure 1. On-Region Characteristics Figure 2. Transfer Characteristics 500 400 *Notes: 1. V_{DS} = 10V 2. 250µs Pulse Test I_b, Drain Current[A] 0 l_b, Drain Current[A] 100 175°C V_{GS} = 15.0V 10.0V -55°C 8.0V 7.0V *Notes: 6.5V 1. 250µs Pulse Test 6.0V 2. $T_{C} = 25^{\circ}C$ 5.5V 10 └ 0.1 1 3 4 5 2 V_{DS}, Drain-Source Voltage[V] V_{GS}, Gate-Source Voltage[V] Figure 4. Body Diode Forward Voltage Figure 3. On-Resistance Variation vs. Variation vs. Source Current **Drain Current and Gate Voltage** and Temperature 2.0 500 Drain-Source On-Resistance 7. 9. 8.1 Reverse Drain Current [A] 100 175°C 25°C $R_{DS(ON)}[m\Omega]$, V_{GS} = 10V 10 V_{GS} = 20V *Notes: <u>,</u> 1. V_{GS} = 0V *Note: T_c = 25°C 2. 250µs Pulse Test 1.2 1 <u>1</u> 0.3 0.4 0 100 200 300 400 500 0.6 0.8 1.0 V_{SD}, Body Diode Forward Voltage [V] I_D, Drain Current [A] **Figure 5. Capacitance Characteristics** Figure 6. Gate Charge Characteristics 10 40000 Ciss Gate-Source Voltage [V] V_{DS} = 12V 8 10000 V_{DS} = 30V Coss V_{DS} = 48V Capacitances [pF] 6 1000 *Note: 1. V_{GS} = 0V 2. f = 1MHz V_{GS}, Crss 2 $C_{iss} = C_{gs} + C_{gd} (C_{ds} = shorted)$ $C_{oss} = C_{ds} + C_{gd}$ 100 *Note: I_D = 100A C_{rss} = C_{gd} 50 0 30 150 60 90 120 0.1 1 10 60 0 Q_g, Total Gate Charge [nC] V_{DS}, Drain-Source Voltage [V] ©2011 Fairchild Semiconductor Corporation 3 FDP020N06B Rev. C8

Typical Performance Characteristics

25°C

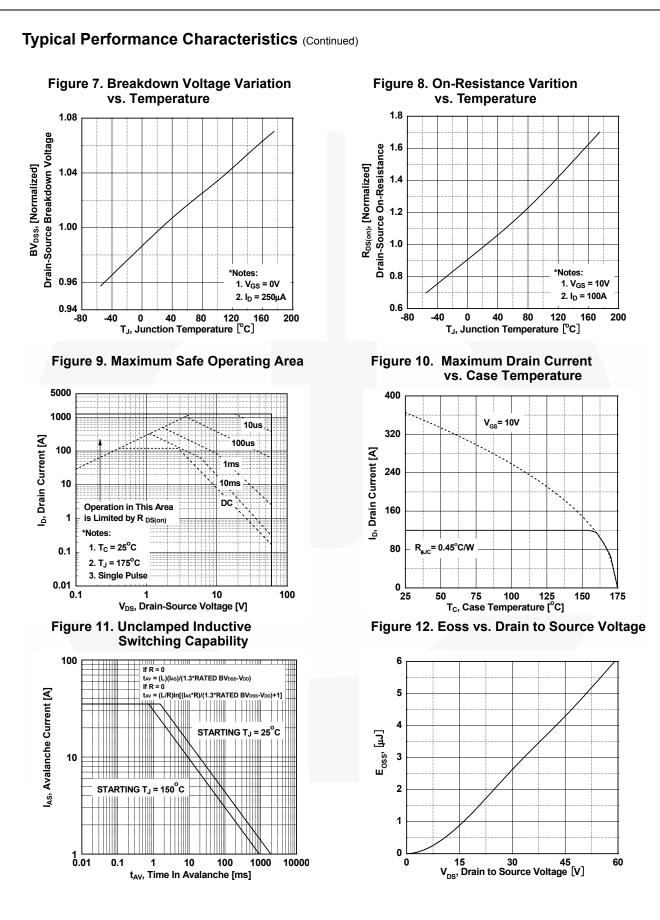
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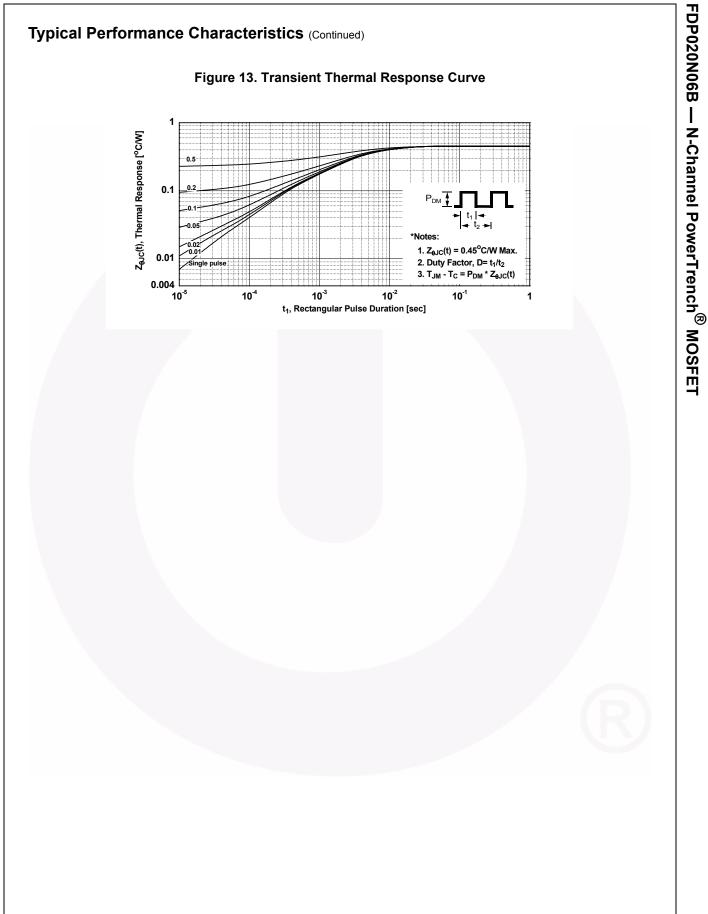
1.2 1.3

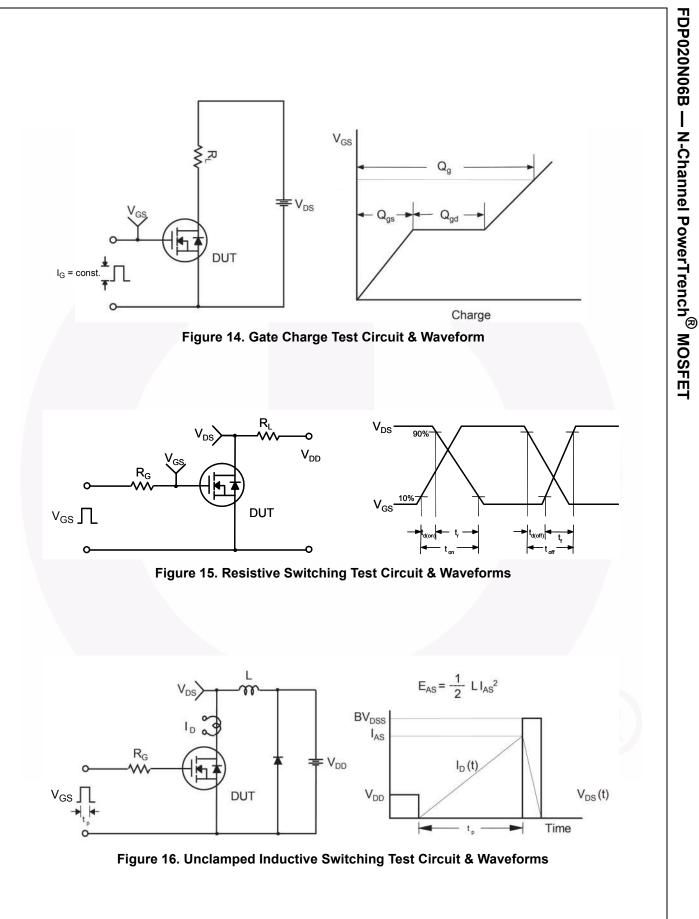
180

210



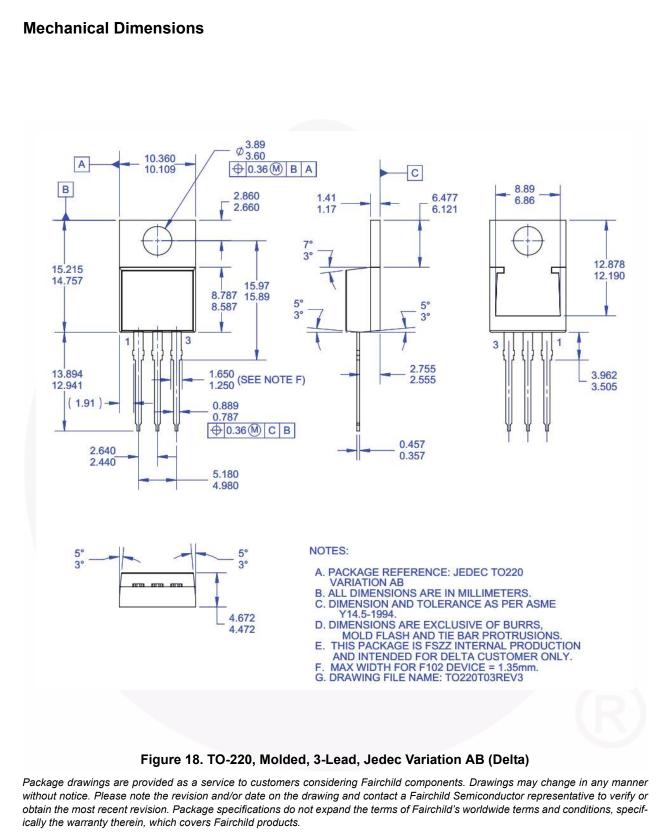
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DUT + v_{DS} a ۱_{SD} م L Driver R_G, Same Type as DUT L F ∨_{DD} $\prod V_{GS}$ • dv/dt controlled by R_{G} • I_{SD} controlled by pulse period Î Gate Pulse Width V_{GS} D = Gate Pulse Period 10V (Driver) I_{FM}, Body Diode Forward Current I _{SD} di/dt (DUT) I_{RM} Body Diode Reverse Current V_{DS} (DUT) Body Diode Recovery dv/dt V_{SD} V_{DD} Body Diode Forward Voltage Drop Figure 17. Peak Diode Recovery dv/dt Test Circuit & Waveforms

FDP020N06B — N-Channel PowerTrench[®] MOSFET



http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TT220-0I3

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